SLOVENSKI STANDARD
SIST EN 60749-19:2004/A1:2010

01-november-2010

Polprevodniški elementi - Metode za mehansko in klimatsko preskušanje - 19. del: Strižna trdnost čipov - Dopolnilo A1 (IEC 60749-19:2003/A1:2010)

Semiconductor devices - Mechanical and climatic test methods - Part 19: Die shear strength (IEC 60749-19:2003/A1:2010)

Halbleiterbauelemente - Mechanische und klimatische Prüfverfahren - Teil 19: Prüfung der Chip-Bondfestigkeit (IEC 60749-19:2003/A1:2010)

Dispositifs à semiconducteurs - Méthodes d'essais mécaniques et climatiques - Partie 19: Résistance de la pastille au cisaillement (CEI 60749-19:2003/A1:2010)

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Ta slovenski standard je istoveten z: EN 60749-19:2003/A1:2010

ICS:

31.080.01	Polprevodniški elementi (naprave) na splošno	Semiconductor devices in general

SIST EN 60749-19:2004/A1:2010 en

2003-01.Slovenski inštitut za standardizacijo. Razmnoževanje celote ali delov tega standarda ni dovoljeno.

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EUROPEAN STANDARD

NORME EUROPÉENNE

EUROPÄISCHE NORM

EN 60749-19/A1

September 2010

ICS 31.080.01

English version

Semiconductor devices - Mechanical and climatic test methods - Part 19: Die shear strength

(IEC 60749-19:2003/A1:2010)

Dispositifs à semiconducteurs -
Méthodes d'essais mécaniques
et climatiques -
Partie 19: Résistance de la pastille
au cisaillement
(CEI 60749-19:2003/A1:2010)

Halbleiterbauelemente -
Mechanische und klimatische
Prüfverfahren -
Teil 19: Prüfung der Chip-Bondfestigkeit
(IEC 60749-19:2003/A1:2010)

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2bba2dffbced/sist-en-60749-19-2004-a1-2010

This amendment A1 modifies the European Standard EN 60749-19:2003; it was approved by CENELEC on 2010-09-01. CENELEC members are bound to comply with the CEN/CENELEC Internal Regulations which stipulate the conditions for giving this amendment the status of a national standard without any alteration.

Up-to-date lists and bibliographical references concerning such national standards may be obtained on application to the Central Secretariat or to any CENELEC member.

This amendment exists in three official versions (English, French, German). A version in any other language made by translation under the responsibility of a CENELEC member into its own language and notified to the Central Secretariat has the same status as the official versions.

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CENELEC

European Committee for Electrotechnical Standardization
Comité Européen de Normalisation Electrotechnique
Europäisches Komitee für Elektrotechnische Normung

Management Centre: Avenue Marnix 17, B - 1000 Brussels

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Ref. No. EN 60749-19:2003/A1:2010 E

SIST EN 60749-19:2004/A1:2010

Foreword

The text of document 47/2016/CDV, future amendment 1 to IEC 60749-19:2003, prepared by IEC TC 47, Semiconductor devices, was submitted to the IEC-CENELEC parallel vote and was approved by CENELEC as amendment A1 to EN 60749-19:2003 on 2010-09-01.

Attention is drawn to the possibility that some of the elements of this document may be the subject of patent rights. CEN and CENELEC shall not be held responsible for identifying any or all such patent rights.

The following dates were fixed:

– latest date by which the amendment has to be implemented at national level by publication of an identical national standard or by endorsement	(dop)	2011-06-01
– latest date by which the national standards conflicting with the amendment have to be withdrawn	(dow)	2013-09-01

Endorsement notice

The text of amendment 1:2010 to the International Standard IEC 60749-19:2003 was approved by CENELEC as an amendment to the European Standard without any modification.

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IEC 60749-19

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INTERNATIONAL STANDARD

NORME INTERNATIONALE

AMENDMENT 1
AMENDEMENT 1

Semiconductor devices – Mechanical and climatic test methods – Part 19: Die shear strength

iTeh STANDARD PREVIEW
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Dispositifs à semiconducteurs – Méthodes d'essais mécaniques et climatiques – Partie 19: Résistance de la pastille au cisaillement

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FOREWORD

This amendment has been prepared by IEC technical committee 47: Semiconductor devices.

The text of this amendment is based on the following documents:

CDV	Report on voting
47/2016/CDV	47/2060/RVC

Full information on the voting for the approval of this amendment can be found in the report on voting indicated in the above table.

The committee has decided that the contents of this amendment and the base publication will remain unchanged until the stability date indicated on the IEC web site under "http://webstore.iec.ch" in the data related to the specific publication. At this date, the publication will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
- amended.

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1 Scope

SIST EN 60749-19:2004/A1:2010

Number the existing 'NOTE' as 'NOTE 1' and add the following "NOTE 2" below "NOTE 1":

https://standards.iteh.ai/catalog/standards/sist/f5c45852-136a-4f52-b25f-2bba2dffbced/sist-en-60749-19-2004-a1-2010

"NOTE 2 In cavity packages, die shear strength is measured in order to assure the strength of the die attachment within the cavity.

In non-cavity packages, such as plastic encapsulated packages, die bonding is used to prevent die movement until the resin mould is completely cured. Normally, specification of the die shear strength and the minimum adhesion area of die bond after moulding are unnecessary, except in the following circumstances:

– when the die needs to be electrically connected to die pad;

– when heat from the die needs to be diffused through the die bond."